**BICMOS LSI** 

LV9005M



# **Optical Sensor Switch IC**

### Overview

The LV9005M is an optical sensor switch IC that is fabricated in a medium breakdown voltage BiCMOS process. The LV9005M circuit structure includes a highgain optical sensor amplifier, a comparator, an oscillator circuit, output drivers, LED drivers, and a synchronous detection and delay circuit. The use of this IC and a minimal number of external components allows the implementations of multifunction high-sensitivity applications that previously would have only been possible with a custom optical-switch IC.

## **Applications**

- Factory automation (detectors for many types of parts and products)
- Home security (doorway and window sensors)
- Office automation equipment

## **Functions and Features**

- Can be used with a wide range of supply voltages; from 5 to 30 V.
- Low power
- Outputs can be selected as PNP or NPN circuit types.
- Built-in high-gain amplifier
- Built-in stability and output display functions

# **Specifications**

#### Absolute Maximum Ratings at $Ta = 25^{\circ}C$

- Supports both reflection and through type applications, and supports both sense on light and sense on dark applications.
- Built-in OCP and power on reset functions
- Built-in three-level comparator
- Synchronous detection scheme adopted for robust performance in the presence of ambient and scattered light.
- External photodiode detection scheme allows the LV9005M to support a wide range of application areas.
- Miniature flat package supports high density printed circuit board mounting.

# **Package Dimensions**

unit: mm

#### 3112-MFP24S



#### SANYO: MFP24S

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V <sub>CC</sub> max		33	V
LD pin voltage	V <sub>LD</sub>		33	V
Allowable power dissipation	Pd max		425	mW
Operating temperature	Topr		-20 to +85	°C
Storage temperature	Tstg		-40 to +125	°C

#### Allowable Operating Ranges at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V <sub>CC</sub>		4.5 to 30	V
LD pin voltage	V <sub>LD</sub>	High breakdown voltage input pins	V <sub>CC</sub> to 0	V

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# Electrical Characteristics at Ta = $25^{\circ}$ C, V<sub>CC</sub> = 12 V (unless otherwise specified)

Parameter	Symbol	Conditions	min	typ	max	Unit
Preamplifier gain	V <sub>G1</sub>	With a 20 k $\Omega$ input series resistance, f = 200 kHz (sine wave)	15	18	21	dB
Main amplifier gain	V <sub>G2</sub>	f = 200 kHz (sine wave)	45	48	51	dB
Regulated power supply	V <sub>REG</sub>	V <sub>CC</sub> = 5 V, 5 mA DC load	3.72	4.0	4.28	V
Current drain	Icc	Measured in the specified circuit*		3.0	4.5	mA
Input resistance	Z <sub>IN</sub>		8.5	10	11.5	kΩ
[LED Output Block]						
Pulse level	$V_{LEH}$	With a 1 k $\Omega$ external resistor	2.9	3.2	3.6	V
Pulse period	T <sub>LE</sub>	C <sub>OSC</sub> = 4700 pF	300	380	460	μs
Pulse width	T <sub>PW</sub>	50%	4.2	5.2	6.2	μs
[Overcurrent Detection Voltage]						
PNP output (source)	OCP (P)	External transistor = PNP	V <sub>CC</sub> – 1.1	V <sub>CC</sub> – 1.35	V <sub>CC</sub> – 1.6	V
NPN output (sink)	OCP (N)	External transistor = NPN	1.10	1.35	1.75	V
Comparator detection level (low)	COMPL		0.33	0.44	0.55	V
Comparator detection level (middle)	COMP <sub>M</sub>		0.60	0.74	0.88	V
Comparator detection level (high)	COMPH		1.03	1.16	1.30	V
LG current	I <sub>LG</sub>		2.05	2.65	3.25	mA
LR current	I <sub>LR</sub>		1.12	1.72	2.32	mA
PNP drive current (source)	I <sub>SRC</sub>		1.80	2.85	3.80	mA
NPN drive current (sink)	I <sub>SNK</sub>		1.90	2.95	3.90	mA
Main amplifier output DC voltage	V <sub>OUT2</sub>		1.20	1.40	1.56	V
RT input high voltage	V <sub>IH</sub> 1		4.0			V
RT input low voltage	V <sub>IL</sub> 1				1.0	V
LD input high voltage	V <sub>IH</sub> 2	High breakdown voltage input pins	4.0			V
LD input low voltage	V <sub>IL</sub> 2	High breakdown voltage input pins			1.3	V
P/N input high voltage	V <sub>PNH3</sub>		4.0			V
P/N input low voltage	V <sub>PNL3</sub>				1.0	V



Note: \* Current drain test circuit

## **Design Specifications**

Parameter	Symbol	Conditions	Ratings	Unit
Synchronization pull-in range	PIR	T <sub>EL</sub> = LED pulse period, transmission mode	0.55 T <sub>LE</sub> to 1.45 T <sub>LE</sub>	μs
Power on reset	T <sub>POR</sub>		13.5	ms
Response time	Т <sub>D</sub>	Oscillator external capacitor C <sub>OCP</sub> = 4700 pF	2 T <sub>LE</sub>	μs
Oscillator period	T <sub>OSC</sub>	Oscillator external capacitor C <sub>OCP</sub> = 4700 pF	380	μs
Hysteresis	V <sub>H</sub>		0.7 +0.2 -0.15	Vp-p
[OCP Pulse]				
Pulse period	T <sub>OCP (N)</sub>		7.0	ms
Pulse width	T <sub>OCPW (N)</sub>		55	μs
Pulse period	T <sub>OCP (P)</sub>	C <sub>OCP</sub> = 22000 pF	7.0	ms
Pulse width	T <sub>OCPW (P)</sub>		55	μs





# **Functional Description**

Item	Symbol	Description		
R/T SW	R/T	Reflection/through switching. *: A separate illumination oscillator is used in transmission mode.		
Reflect	R	Input voltage = high (V <sub>REG</sub> ) or open		
Through	Т	Input voltage = low (GND)		
L/D SW	L/D	Light/dark switching		
Light	L	Input voltage = high (V <sub>CC</sub> ) or open		
Dark	D	Input voltage = low (GND)		
P/N SW	P/N	Output PNP/NPN switching		
PNP mode	PNP	Input voltage = high (V <sub>REG</sub> ) or open		
NPN mode	NPN	Input voltage = low (GND)		
Output protection		Built-in overcurrent (load short) protection circuit		
Comparator and display ranges		H H Green LED lights H H H H H H H H H H H H H H H H H H H		
Output type		NPN, PNP, two outputs		
Mode relationship		Light on mode $\rightarrow$ Light detected: output on, dark detected: output off		
		Dark on mode $\rightarrow$ Light detected: output off, dark detected: output on		

## Pin Assignment



#### **Pin Functions**

Pin No.	Symbol	I/O circuit type	Notes
3	IN1	IN1	Amplifier first stage input (Capacitor coupled to the external circuit.)
4	Z <sub>IN</sub>	Z <sub>IN</sub> ₹10kû  A02540	Photodiode series (load) resistance (Used when not used with an external resistor.)
5	OUT1	2000 W	Amplifier first stage output
6	IN2	3000 IN2 W 402542	Output amplifier input
8	OUT2	To comparator To comparator UT2 W OUT2 3002 A02643	Output amplifier output
9	M <sub>IN</sub>	MIN 3000 Comparator	Comparator middle input (This pin sets the hysteresis. The hysteresis is maximum when this pin is open, and minimum when this pin is shorted to pin 8.)
10	L/D	Light on mode $\rightarrow V_{CC}$ Dark on mode $\rightarrow 0 V$	Light/dark mode switching This pin has a built-in noise filter (delay time: 2T <sub>LE</sub> )
11	R/T	Reflect mode $\rightarrow$ 4 V (V <sub>REG</sub> ) or open Through mode $\rightarrow$ 0 V	Reflect/through mode switching

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Pin No.	Function	I/O circuit type	Notes
12	P/N	PNP mode $\rightarrow$ 4 V (V <sub>REG</sub> ) or open NPN mode $\rightarrow$ 0 V	PNP/NPN switching
14	LED OUT	HOQ W LED OUT	Light source LED drive output
15	LR		Red LED (display) connection
16	LG	LG 	Green LED (display) connection
18	C <sub>OSC</sub>		Oscillator capacitor connection
19	PW	COSC , PW 	Light source LED pulse width adjustment (Connect pins 18 and 19 through an external resistor to narrow the pulse width from the illumination LED.)
20	V <sub>REG</sub>	V <sub>REG</sub> = V <sub>RP</sub> (Pin 2)= 4 V	Regulator output
21	C <sub>OCP</sub>		OCP pulse oscillator capacitor connection
22	NPN		NPN transistor connection output
23	PNP	VCC \$10 k 0 PNP output A02650	PNP transistor connection output



#### Equivalent Circuit Block Diagram



2. The photodiode and LEDs specified here are examples only. The devices actually used should be chosen based on the particular application.

3. The OCP detection level is determined by the voltage across RL plus the Tr2 (or TR1) VBE voltage.



#### Sample Printed Circuit Board Pattern (copper side)

#### Sample LV9005M Applications

Through type optoelectronic switch



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